



CEP08N6A/CEB08N6A CEF08N6A

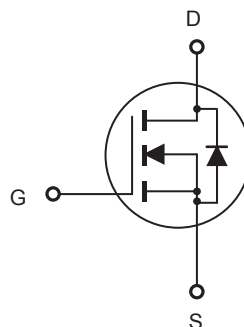
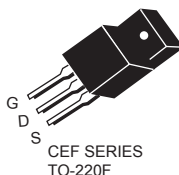
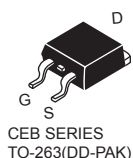
N-Channel Enhancement Mode Field Effect Transistor

PRELIMINARY

FEATURES

Type	V _{DSS}	R _{DS(ON)}	I _D	@V _{GS}
CEP08N6A	600V	1.25Ω	7.5A	10V
CEB08N6A	600V	1.25Ω	7.5A	10V
CEF08N6A	600V	1.25Ω	7.5A ^d	10V

- Super high dense cell design for extremely low R_{DS(ON)}.
- High power and current handling capability.
- Lead-free plating ; RoHS compliant.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit		Units
		TO-220/263	TO-220F	
Drain-Source Voltage	V _{DS}	600		V
Gate-Source Voltage	V _{GS}	±30		V
Drain Current-Continuous @ T _C = 25 C @ T _C = 100°C	I _D	7.5	7.5	A
		5.2	5.2 ^d	A
Drain Current-Pulsed ^a	I _{DM} ^e	30	30 ^d	A
Maximum Power Dissipation @ T _C = 25°C - Derate above 25°C	P _D	150	48	W
		1	0.3	W/°C
Single Pulsed Avalanche Energy ^h	E _{AS}	245		mJ
Single Pulsed Avalanche Current ^h	I _{AS}	7		A
Operating and Store Temperature Range	T _J , T _{stg}	-55 to 175		°C

Thermal Characteristics

Parameter	Symbol	Limit		Units
Thermal Resistance, Junction-to-Case	R _{θJC}	1	3.1	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	65	°C/W

This is preliminary information on a new product in development now .
Details are subject to change without notice .

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<http://www.cetsemi.com>



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Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	600			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V$			1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 30V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -30V, V_{DS} = 0V$			-100	nA
On Characteristics ^b						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 3.1A$		1.05	1.25	Ω
Dynamic Characteristics ^c						
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0\text{ MHz}$		1280		pF
Output Capacitance	C_{oss}			120		pF
Reverse Transfer Capacitance	C_{rss}			11		pF
Switching Characteristics ^c						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300V, I_D = 7A,$ $V_{GS} = 10V, R_{GEN} = 25\Omega$		23	46	ns
Turn-On Rise Time	t_r			8	16	ns
Turn-Off Delay Time	$t_{d(off)}$			55	110	ns
Turn-Off Fall Time	t_f			8	16	ns
Total Gate Charge	Q_g	$V_{DS} = 480V, I_D = 7A,$ $V_{GS} = 10V$		21	27	nC
Gate-Source Charge	Q_{gs}			5		nC
Gate-Drain Charge	Q_{gd}			5		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current	I_S ^f				7	A
Drain-Source Diode Forward Voltage ^b	V_{SD}	$V_{GS} = 0V, I_S = 7A$ ^g			1.5	V
Notes : a.Repetitive Rating : Pulse width limited by maximum junction temperature . b.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$. c.Guaranteed by design, not subject to production testing. d.Limited only by maximum temperature allowed . e.Pulse width limited by safe operating area . f.Full package $I_{S(max)} = 4A$. g.Full package V_{SD} test condition $I_S = 4A$. h.L = 10mH, $I_{AS} = 7A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25\text{ }^{\circ}C$.						



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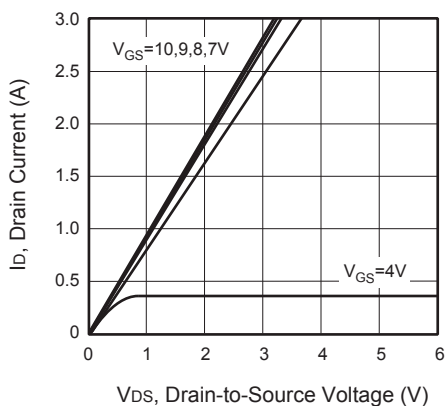


Figure 1. Output Characteristics

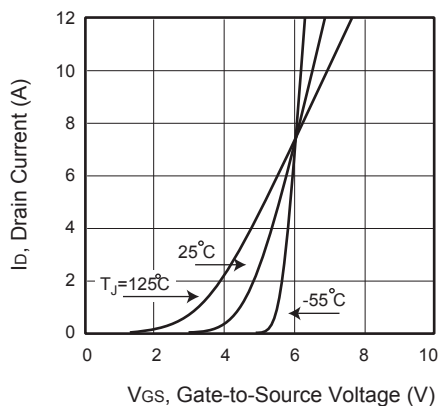


Figure 2. Transfer Characteristics

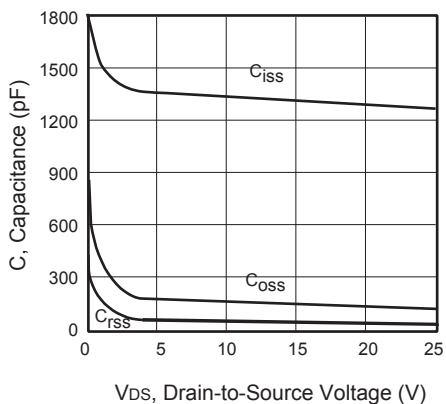


Figure 3. Capacitance

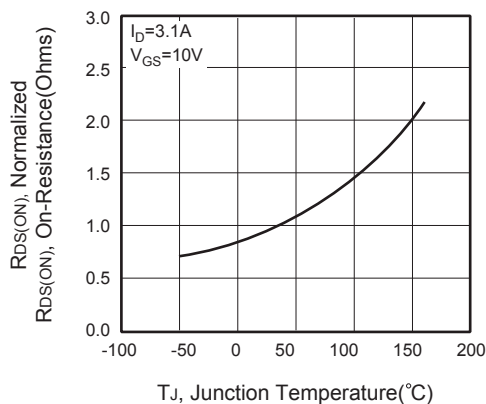


Figure 4. On-Resistance Variation with Temperature

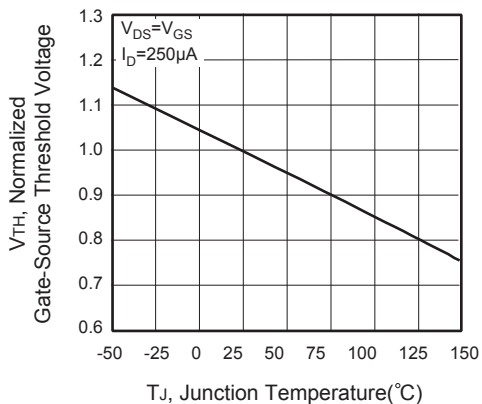


Figure 5. Gate Threshold Variation with Temperature

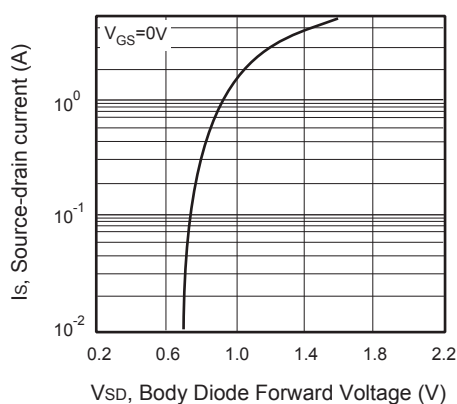


Figure 6. Body Diode Forward Voltage Variation with Source Current

